

UNISONIC TECHNOLOGIES CO., LTD

UH11K

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

SOT-363

DUAL BIAS RESISTOR TRANSISTORS

DESCRIPTION

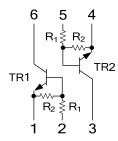
The UTC **UH11K** is a dual bias resistor transistors, it uses UTC's advanced technology to provide customers with saving board space, reducing component count, etc.

The UTC **UH11K** is suitable for low power surface mount applications, etc.

FEATURES

- * Reducing component count
- * Saving board space

EQUIVALENT CIRCUIT

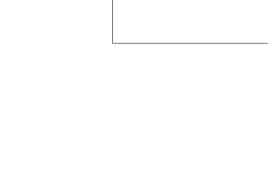


ORDERING INFORMATION

Ordering Number		Package		Pin Assignment					Deaking	
				2	3	4	5	6	Packing	
UH11KG-AL6-R	SOT-363		E1	B1	C2	E2	B2	C1	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source										
UH11KG-AL6-R (1)Packing Type (2)Package Type (3)Green Package		(1) R: Tape Reel(2) AL6: SOT-363(3) G: Halogen Free and Lead Free								

MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Collector Current	lc	100	mA
Power Dissipation	PD	150	mW
Junction Temperature	TJ	-55~+150	°C
Storage Temperature	T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =10μΑ, I _E =0	50			V			
Collector-Emitter Breakdown Voltage (Note 1)	BV _{CEO}	I _C =2.0mA, I _B =0	50			V			
Collector-Base Cutoff Current	I _{CBO}	V _{CB} =50V, I _E =0			100	nA			
Collector-Emitter Cutoff Current	I _{CEO}	V _{CE} =50V, I _B =0			500	nA			
Emitter-Base Cutoff Current	I _{EBO}	V _{EB} =6.0V, I _C =0			0.5	mA			
ON CHARACTERISTICS (Note 2)									
DC Current Gain	h _{FE}	V _{CE} =10V, I _C =5.0mA	35	60					
Output Voltage (on)	Vol	V_{CC} =5.0V, V_{B} =2.5V, R_{L} =1.0 k Ω			0.2	V			
ON CHARACTERISTICS (Note 2)									
Input Resistor	R ₁		7.0	10	13	kΩ			
Resistor Ratio	R_1/R_2		0.8	1.0	1.2	kΩ			

Notes: 1. Pulse Test: Pulse Width<300µs, Duty Cycle<2.0%

2. Pulse Test: Pulse Width<300ms, Duty Cycle<2.0%



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